

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Docket Number (Optional)

OIP.024D2

Application Number

~~NEW~~

Applicant(s)

Akira Takahashi

10/779752

Filing Date

February 18, 2004

Group Art Unit

2813
~~Unknown~~

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TSP	A	5,899,721	5/1999	Gardner et al.	—	—	—
↓	B	6,245,625	6/2001	Gau	—	—	—
↓	C	6,495,889	12/2002	Takahashi	—	—	—
TSP	D	5,610,092	3/1997	Tasaka	—	—	—

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
TSP	E	10-4190	1/06/1998	Japan				
TSP	F	2000-49340	2/18/2000	Japan				
TSP	G	9-45908	2/14/1997	Japan				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

TSP	H	Tomohisa Mizuno et al., "Hot-Carrier Injection Suppression Due to the Nitride-Oxide LDD Spacer Structure," IEEE Transactions on Electron Devices, Vol. 38, No. 3, March 1991, pages 548-591.
TSP	I	F.C. Hsu et al., "Structure-Enhanced MOSFET Degradation Due to Hot-Electron Injection," IEEE Electron Device Letters, Vol. EDL-5, No. 3, March 1984, pages 71-74.

EXAMINER



DATE CONSIDERED

4/11/05

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION
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Docket Number (Optional) OIP.024D		Application Number NEW
Applicant(s) Akira Takahashi		10/779 752
Filing Date February 18, 2004		Group Art Unit Unknown 2813

U.S. PATENT DOCUMENTS


*EXAMINER INITIAL.	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

TSP	J	Ahn et al., "Hot-Carrier degradation of single-drain PMOSFET's with differing sidewall spacer thicknesses", IEEE electron device letters, Vol. 13, 04/1992, pp. 711-713.

EXAMINER 	DATE CONSIDERED 4/11/05
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